

L Number	Hits	Search Text	DB	Time stamp
-	1	quartz near5 single adj crystal\$4 same diffraction near2 peak	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 13:01
-	33	quartz same buffer same (gan or zno or gallium adj nitride or zinc adj oxide)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 12:56
-	13	quartz near5 crystal\$4 same diffraction near2 peak	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 13:06
-	55	quartz near5 epitax\$4 near3 (film or layer)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 13:41
-	9	quartz near2 epitax\$4 near3 (film or layer)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 13:44
-	17	quartz same buffer near4 (gan or gallium adj nitride or zno or zinc adj oxide)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 13:47
-	1	(silicon adj (dioxide or oxide)) near4 (epitax\$4 or crystal\$4) same buffer near4 (gan or gallium adj nitride or zno or zinc adj oxide)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 13:49
-	46	(silicon adj (dioxide or oxide)) adj (epitax\$4 or crystal\$4) near2 (film or layer)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 13:54
-	1	quartz adj (epitax\$4 or crystal\$4) near2 (film or layer) same buffer	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 13:58
-	1	quartz adj (epitax\$4) near2 (film or layer)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 13:59
-	12	quartz adj (epitax\$4)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 14:00
-	13	quartz same (gan or gallium adj nitride or zno or zinc adj oxide) near3 buffer	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 14:01
-	52	oxide same rock near3 crystal\$4 same quartz	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 14:33

-	4	quartz adj (film or layer) same buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 14:35
-	75	quartz near2 (film or layer) same buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 14:53
-	12	buffer near2 (Gan or gallium adj nitride or zno or zinc adj oxide) same (quartz)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 14:59
-	1	buffer near2 (Gan or gallium adj nitride or zno or zinc adj oxide) same rock near2 crystal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 15:00
-	65	buffer near2 (Gan or gallium adj nitride or zno or zinc adj oxide) same ("sio.sub.2" or silicon adj oxide or silicon adj oxide) near2 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 15:06
-	9	buffer near2 (Gan or gallium adj nitride or zno or zinc adj oxide) same quartz same quartz not adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 15:17
-	58	(gallium adj nitride or gan or zinc adj oxide or zno) same (quartz near2 (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 15:53
-	1	(gallium adj nitride or gan or zinc adj oxide or zno) near2 buffer same (quartz near2 (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 15:21
-	12	(gallium adj nitride or gan or zinc adj oxide or zno) near2 buffer same quartz	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 16:34
-	0	(oxide same rock near3 crystal\$4 same quartz) same (buffer adj1 (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 15:29
-	2	(quartz adj1 (layer or film)) same (buffer adj1 (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 15:32
-	0	(quartz adj1 (layer or film)) same ((gallium adj1 nitride) or Gan!)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 15:33
-	7	(quartz adj1 (layer or film)) same ((zinc adj1 oxide) or Zno!)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 15:34
-	4	quartz adj1 (layer or film) same buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 15:38

-	5	buffer near4 (titanium adj oxide or "tio.sub.2") same (gan or gallium adj nitride or zno or znic adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 15:41
-	4	quartz adj (film or layer) and buffer near2 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 15:58
-	30	quartz adj (film or layer) and buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:15
-	68	tetrabutoxysilane same alkoxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:16
-	63	tetrabutoxysilane same alkoxide same tetramethoxysilane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:16
-	0	tetrabutoxysilane same alkoxide same tetramethoxysilane and 117/\$4.cc1s.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:16
-	2	tetrabutoxysilane same alkoxide same tetramethoxysilane same deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:17
-	2	tetrabutoxysilane same tetramethoxysilane same deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:17
-	27	tetrabutoxysilane same alkoxide same tetramethoxysilane and deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:20
-	0	tetrabutoxysilane same alkoxide same tetramethoxysilane same vapor\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:21
-	1	(gallium adj nitride or gan or zinc adj oxide or zno) near2 buffer same (silicon adj dioxide or silicon adj oxide or "sio.sub.2") near2 crystal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:35
-	87	(gallium adj nitride or gan or zinc adj oxide or zno) same (silicon adj dioxide or silicon adj oxide or "sio.sub.2") near2 crystal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:43
-	16	(gallium adj nitride or gan or zinc adj oxide or zno) near3 buffer and (silicon adj dioxide or silicon adj oxide or "sio.sub.2") near2 crystal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:49
-	75	quartz near2 (film or layer) same buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/25 16:53

-	6	(quartz near2 (film or layer) same buffer) and (gan or gallium adj nitride or zno or zinc adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/25 16:54
-	131	quartz near2 (film or layer) same (gallium adj nitride or gan or zinc adj oxide or zno or buffer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/27 15:36
-	4	quartz near4 (gan or gallium adj nitride or zno or zinc adj oxide) same buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/27 15:38
-	2	quartz near4 (gan or gallium adj nitride or zno or zinc adj oxide) near5 buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/27 15:42
-	20	quartz near4 (gan or gallium adj nitride or zno or zinc adj oxide) near4 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/27 15:50
-	25	quartz near4 (gan or gallium adj nitride or zno or zinc adj oxide) and waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/27 15:51
-	58	quartz near2 (film or layer) same (gan or gallium adj nitride or zinc adj oxide or zno)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 16:19
-	12	quartz near2 (film or layer) and (gan or gallium adj nitride or zinc adj oxide or zno) same buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 15:34
-	7	quartz adj (film or layer) same (gan or gallium adj nitride or zinc adj oxide or zno)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 16:24
-	27	quartz adj (film or layer) and (gan or gallium adj nitride or zinc adj oxide or zno)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 16:34

FILE 'CAPPLUS' ENTERED AT 14:40:00 ON 06 MAR 2003

L1 73 S EPITAX? (1A) QUARTZ
L2 0 S L1 AND BUFFER
L3 0 S L1 AND (GAN OR ZNO)

FILE 'REGISTRY' ENTERED AT 14:42:14 ON 06 MAR 2003

L4 85 S GAN
L5 372 S ZNO

FILE 'CAPPLUS' ENTERED AT 14:42:39 ON 06 MAR 2003

L6 0 S L1 AND (L4 OR L5)
L7 3 S L1 AND NITRIDE
L8 1138 S QUARTZ (2A) FILM
L9 33 S L8 AND (L4 OR L5)
L10 16 S L8 AND BUFFER

FILE 'INSPEC' ENTERED AT 14:58:57 ON 06 MAR 2003

L11 14 S L9
L12 4 S L10
L13 0 S L2
L14 6 S L1

FILE 'REGISTRY' ENTERED AT 15:05:18 ON 06 MAR 2003

L15 1 S QUARTZ/CN

FILE 'CAPPLUS' ENTERED AT 15:05:38 ON 06 MAR 2003

L16 36682 S L15
L17 70 S L16 (2A) (FILM OR EPITAX?)
L18 52 S L17 NOT L1
L19 1 S L18 AND BUFFER
L20 2 S L18 AND (L4 OR L5)
L21 1 S L18 AND NITRIDE
L22 2 S L18 AND (GAN OR ZNO)

FILE 'INSPEC' ENTERED AT 15:09:25 ON 06 MAR 2003

L23 0 S L17

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